

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}$ | I_D $T_A = 25^\circ C$ |
|---------------|--------------------------------|-----------------------------|
| 40V | 30m Ω @ $V_{GS} = 10V$ | 13.7A |
| | 50m Ω @ $V_{GS} = 4.5V$ | 10.6A |

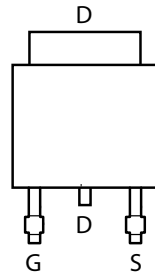
Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

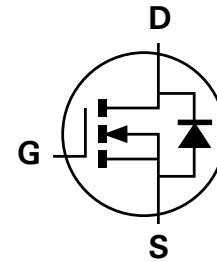
- Backlighting
- DC-DC Converters
- Power management functions



TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Features and Benefits

- Low on-resistance
- Fast switching speed
- “Green” component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

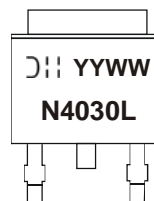
- Case: TO252-3L
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

Ordering Information (Note 1)

| Product | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---------------|---------|--------------------|-----------------|-------------------|
| DMN4030LK3-13 | N4030L | 13 | 16 | 2,500 |

Notes: 1. Diodes, Inc. defines “Green” products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.’s “Green” Policy can be found on our website. For packaging details, go to our website.

Marking Information



⌋⌋⌋ = Manufacturer's Marking
 N4030L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 09 = 2009)
 WW = Week (01 - 53)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

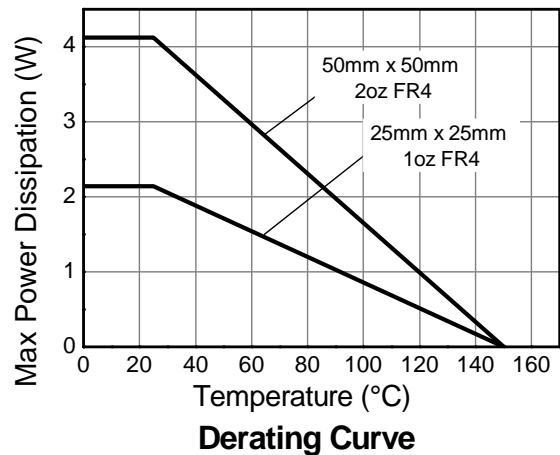
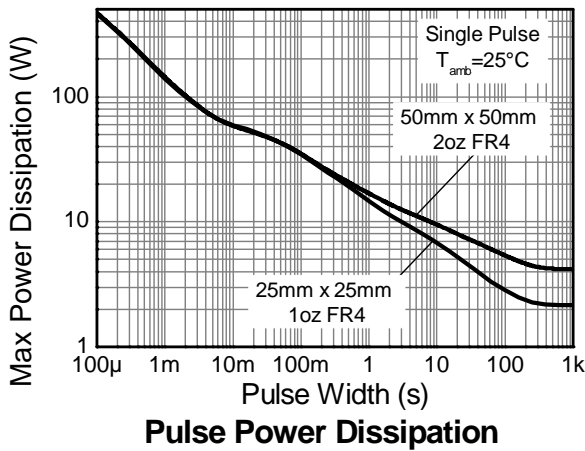
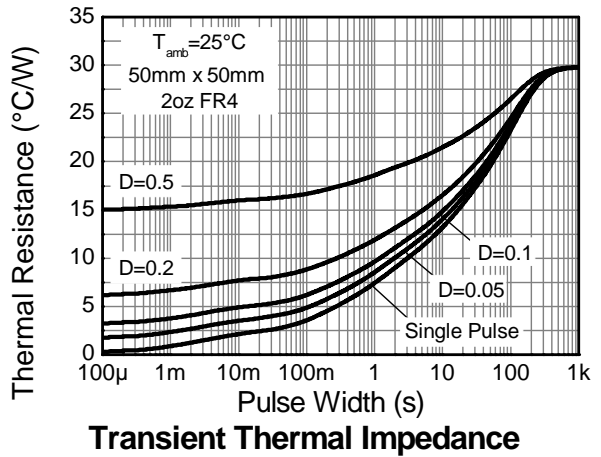
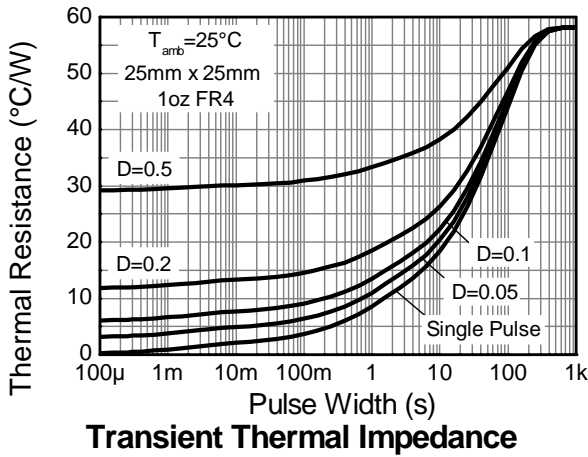
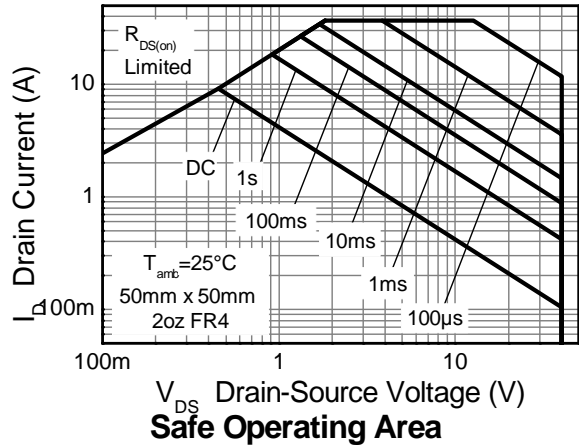
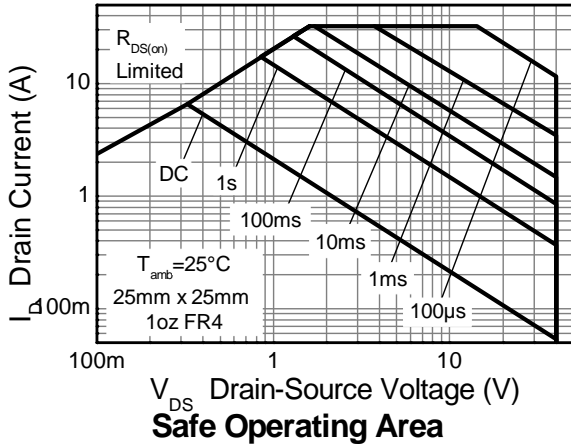
| Characteristic | | | Symbol | Value | Unit |
|--|-----------------------|-----------------------------------|----------|----------|------|
| Drain-Source voltage | | | V_{DS} | 40 | V |
| Gate-Source voltage | | | V_{GS} | ± 20 | V |
| Continuous Drain current | $V_{GS} = 10\text{V}$ | (Note 2) | I_D | 13.7 | A |
| | | $T_A = 70^\circ\text{C}$ (Note 4) | | 10.9 | |
| | | (Note 3) | | 9.4 | |
| Pulsed Drain current | $V_{GS} = 10\text{V}$ | (Note 5) | I_{DM} | 37.7 | A |
| Continuous Source current (Body diode) | | | I_S | 10.7 | A |
| Pulsed Source current (Body diode) | | | I_{SM} | 37.7 | A |

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | | Symbol | Value | Unit |
|---|----------|-----------------|------------|---------------------------|
| Power dissipation Linear derating factor | (Note 3) | P_D | 4.18 | W mW/ $^\circ\text{C}$ |
| | (Note 4) | | 33.4 | |
| | (Note 6) | | 8.9 | |
| | | | 71.4 | |
| | | | 2.14 | |
| Thermal Resistance, Junction to Ambient | (Note 3) | $R_{\theta JA}$ | 17.1 | $^\circ\text{C}/\text{W}$ |
| | (Note 4) | | 29.9 | |
| | (Note 6) | | 14.0 | |
| Thermal Resistance, Junction to Lead | (Note 7) | $R_{\theta JL}$ | 58.4 | |
| Operating and storage temperature range | | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

- Notes:
- AEC-Q101 V_{GS} maximum is $\pm 16\text{V}$.
 - For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as note 3, except the device is measured at $t \leq 10$ sec.
 - Same as note 3, except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 - For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

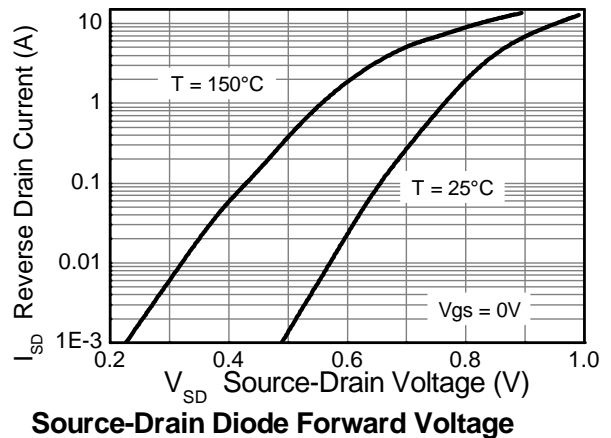
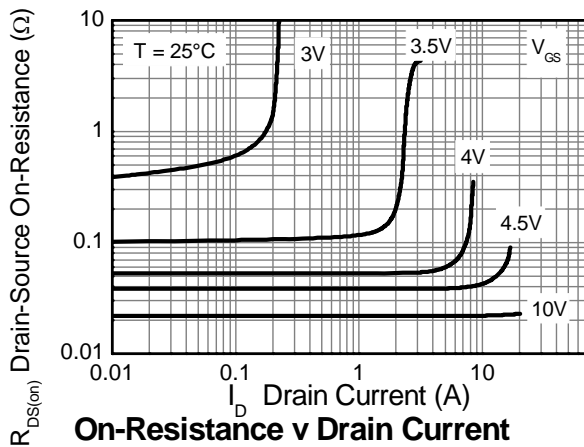
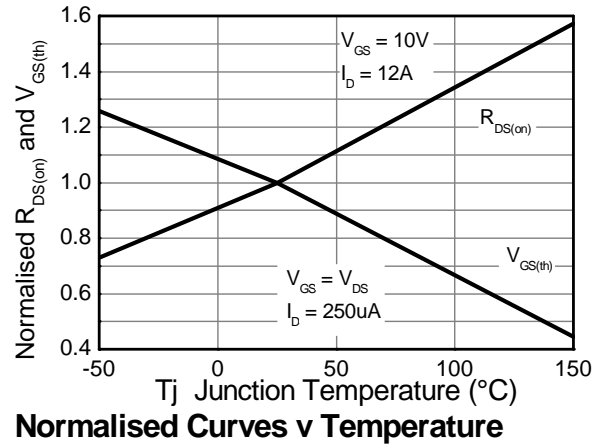
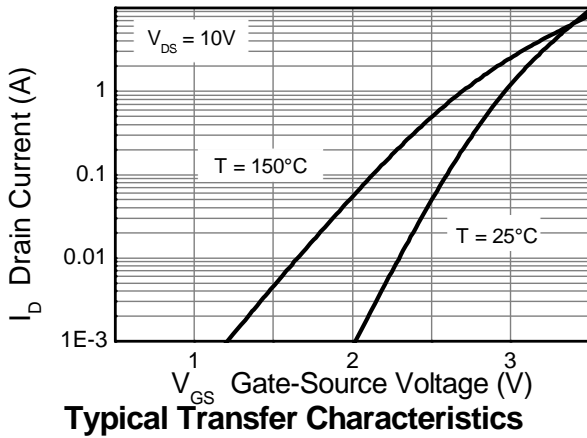
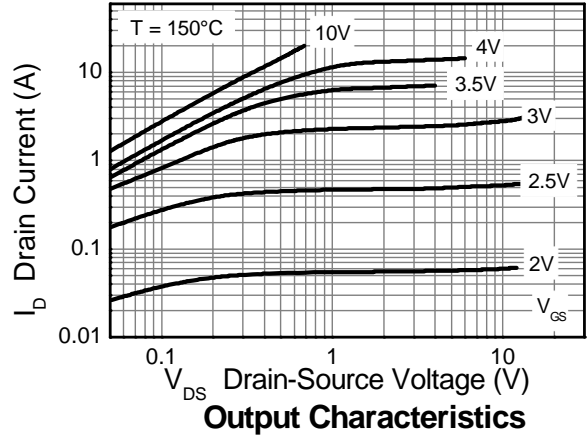
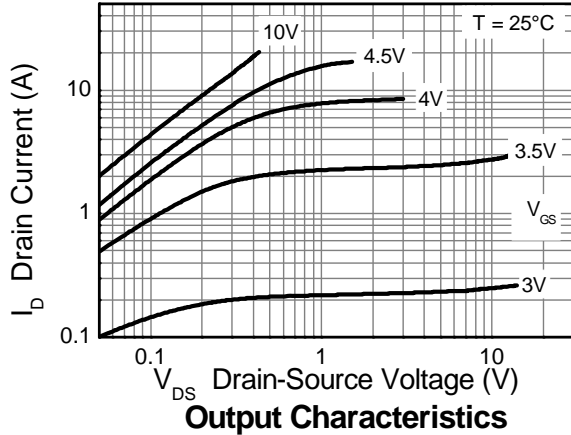


Electrical Characteristics @T_A = 25°C unless otherwise specified

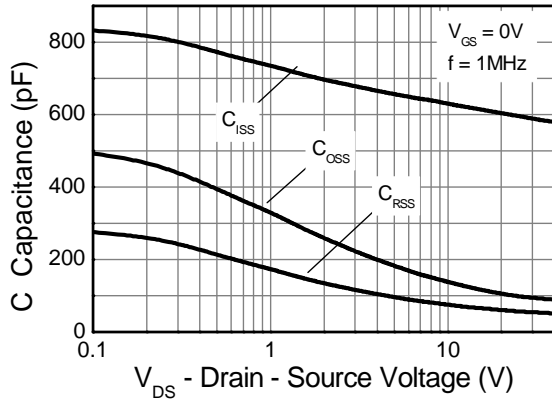
| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition | |
|--|---------------------|-----|-------|-------|------|---|---|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 40 | — | — | V | I _D = 250μA, V _{GS} = 0V | |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | 0.5 | μA | V _{DS} = 40V, V _{GS} = 0V | |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V | |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 1.0 | — | 3.0 | V | I _D = 250μA, V _{DS} = V _{GS} | |
| Static Drain-Source On-Resistance (Note 8) | R _{DS(on)} | — | 0.021 | 0.030 | Ω | V _{GS} = 10V, I _D = 12A | |
| | | | 0.037 | 0.050 | | V _{GS} = 4.5V, I _D = 6A | |
| Forward Transconductance (Notes 8 & 9) | g _{fs} | — | 22.8 | — | S | V _{DS} = 15V, I _D = 12A | |
| Diode Forward Voltage (Note 8) | V _{SD} | — | 0.95 | 1.1 | V | I _S = 12A, V _{GS} = 0V | |
| Reverse recovery time (Note 9) | t _{rr} | — | 135 | — | ns | I _S = 12A, di/dt = 100A/μs | |
| Reverse recovery charge (Note 9) | Q _{rr} | — | 799 | — | nC | | |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | | |
| Input Capacitance | C _{iSS} | — | 604 | — | pF | V _{DS} = 20V, V _{GS} = 0V f = 1MHz | |
| Output Capacitance | C _{oss} | — | 106 | — | pF | | |
| Reverse Transfer Capacitance | C _{rSS} | — | 59.6 | — | pF | | |
| Total Gate Charge (Note 10) | Q _g | — | 6.5 | — | nC | V _{GS} = 4.5V | |
| Total Gate Charge (Note 10) | Q _g | — | 12.9 | — | nC | V _{GS} = 10V | |
| Gate-Source Charge (Note 10) | Q _{gs} | — | 2.3 | — | nC | | V _{DS} = 20V I _D = 12A |
| Gate-Drain Charge (Note 10) | Q _{gd} | — | 3.6 | — | nC | | |
| Turn-On Delay Time (Note 10) | t _{D(on)} | — | 4.2 | — | ns | V _{DD} = 20V, V _{GS} = 10V I _D = 12A, R _G ≅ 6.0Ω | |
| Turn-On Rise Time (Note 10) | t _r | — | 12.4 | — | ns | | |
| Turn-Off Delay Time (Note 10) | t _{D(off)} | — | 13.8 | — | ns | | |
| Turn-Off Fall Time (Note 10) | t _f | — | 10.7 | — | ns | | |

- Notes:
8. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 9. For design aid only, not subject to production testing.
 10. Switching characteristics are independent of operating junction temperatures.

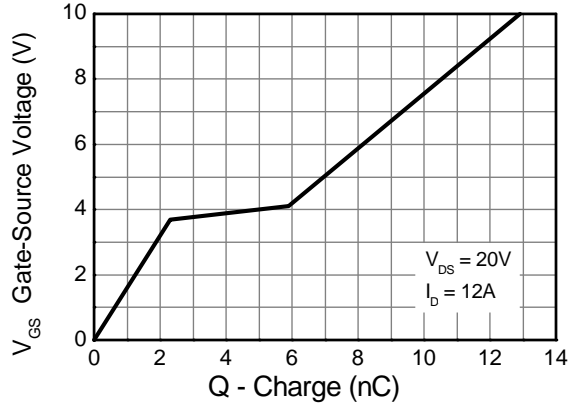
Typical Characteristics



Typical Characteristics - continued

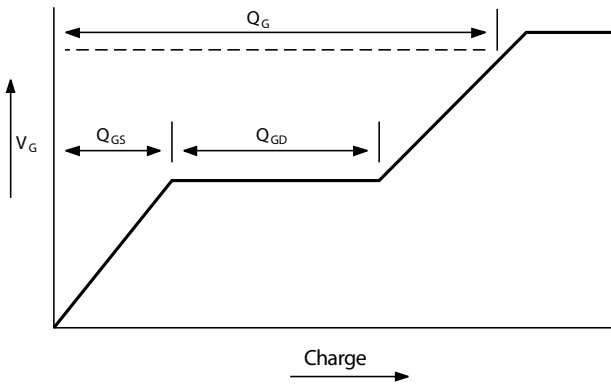


Capacitance v Drain-Source Voltage

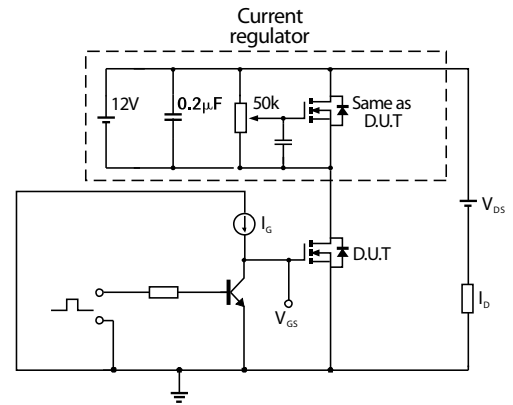


Gate-Source Voltage v Gate Charge

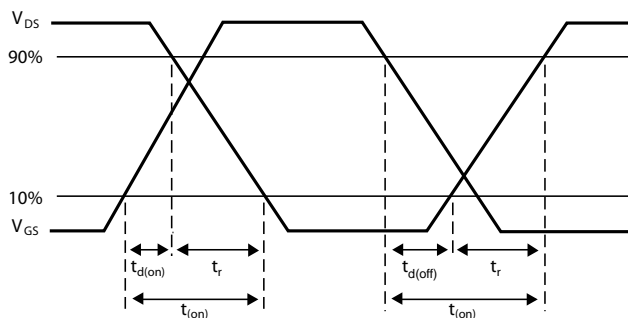
Test Circuits



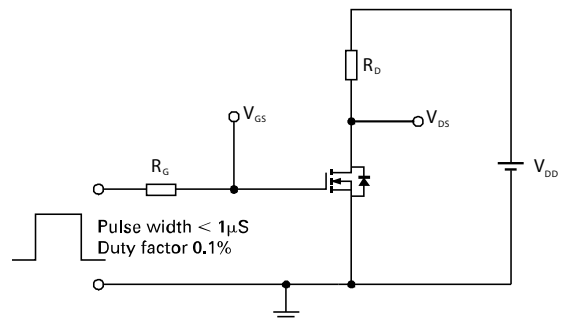
Basic gate charge waveform



Gate charge test circuit

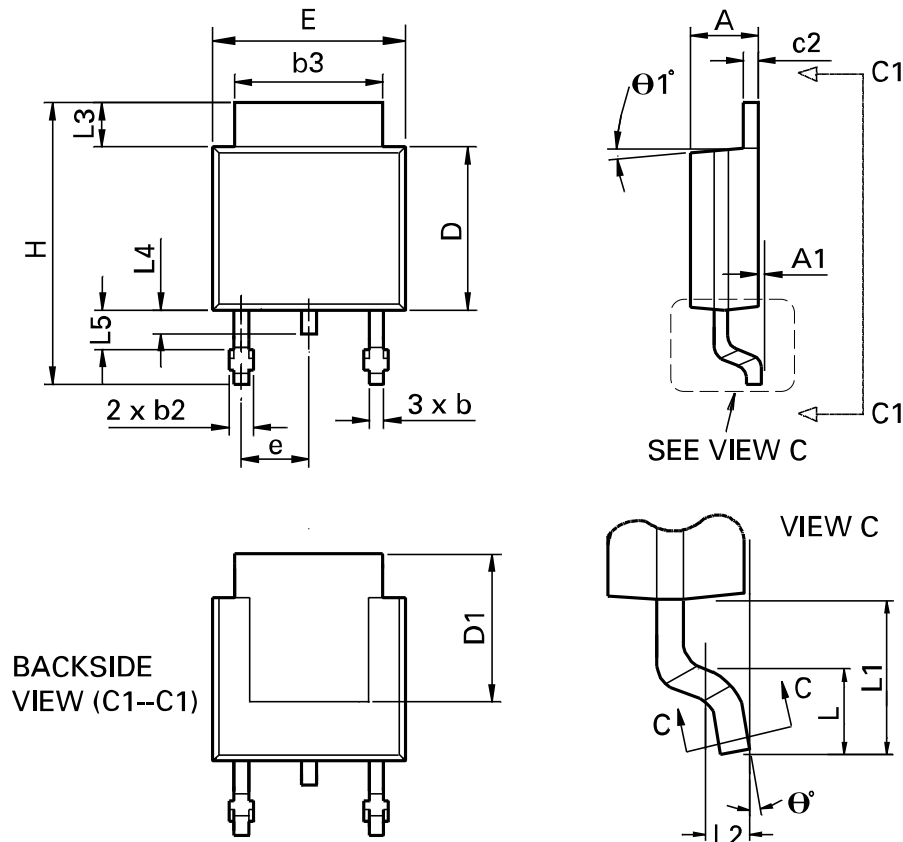


Switching time waveforms



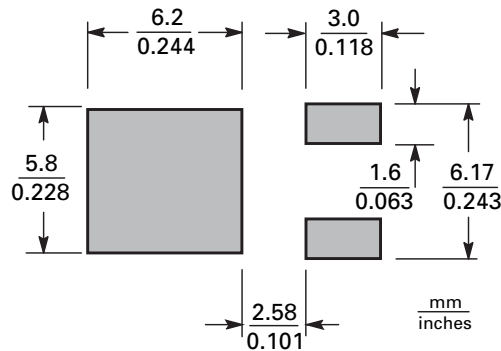
Switching time test circuit

Package Outline Dimensions



| DIM | Inches | | Millimeters | | DIM | Inches | | Millimeters | |
|-----|--------|-------|-------------|-------|------------------|-----------|-------|-------------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max |
| A | 0.086 | 0.094 | 2.18 | 2.39 | e | 0.090 BSC | | 2.29 BSC | |
| A1 | - | 0.005 | - | 0.127 | H | 0.370 | 0.410 | 9.40 | 10.41 |
| b | 0.020 | 0.035 | 0.508 | 0.89 | L | 0.055 | 0.070 | 1.40 | 1.78 |
| b2 | 0.030 | 0.045 | 0.762 | 1.14 | L1 | 0.108 REF | | 2.74 REF | |
| b3 | 0.205 | 0.215 | 5.21 | 5.46 | L2 | 0.020 BSC | | 0.508 BSC | |
| c | 0.018 | 0.024 | 0.457 | 0.61 | L3 | 0.035 | 0.065 | 0.89 | 1.65 |
| c2 | 0.018 | 0.023 | 0.457 | 0.584 | L4 | 0.025 | 0.040 | 0.635 | 1.016 |
| D | 0.213 | 0.245 | 5.41 | 6.22 | L5 | 0.045 | 0.060 | 1.14 | 1.52 |
| D1 | 0.205 | - | 5.21 | - | θ_1° | 0° | 10° | 0° | 10° |
| E | 0.250 | 0.265 | 6.35 | 6.73 | θ° | 0° | 15° | 0° | 15° |
| E1 | 0.170 | - | 4.32 | - | - | - | - | - | - |

Suggested Pad Layout



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